

Reliability qualification information

Stress	Conditions	Duration	Quantity	Rejects
Stress				
Pre and Post stress	$T_{amb} = 25$ °C	N/A	All parts	See
electrical test				below
	JESD22-A113	24 hours		
PC	Bake T _{amb} = 125°C		924	0
Preconditioning	Soak T _{amb} = 85°C, RH = 85%	168 hours	924	U
_	reflow	3 cycles		
HTRB	MIL-STD-750-1			
High temperature	$T_j = T_j \text{ max}$, $V_{DS} = 80\%$ of rated	1000 hours	231	0
reverse bias	Voltage M1039 Method A			
HTGB	JESD22-A108			
High temperature gate	$T_j = T_j \text{ max}, V_{GS} = 20V(SL), 16V$	1000 hours	231	0
bias	(LL)			
TC	JESD22-A104	500 cycles	231	0
Temperature Cycling	-55°C to 150°C	300 Cycles	231	
UHAST	JESD22-A118			
Unbiased highly	$T_{amb} = 130$ °C, RH = 85%	96 hours	231	0
accelerated stress test	Pressure = +2.27atm			
HAST*	JESD22-A110			
Highly accelerated	$T_{amb} = 130$ °C, RH = 85%	96 hours		0
stress test	$V_{DS} = 80\%$ of rated voltage		231	
H3TRB*	JESD22-A101		231	
Temperature Humidity	$T_{amb} = 85^{\circ}C$, RH = 85%	1000 hours		
bias	$V_{DS} = 80\%$ of rated voltage			
IOL	MIL-STD-750 method 1037			
Intermittent operating	ΔTj = 80°C	5000 cycles	231	0
life				1
RSH	JECD 22 A 1 1 1 (CMD)			
Resistance to solder	JESD22-A111 (SMD)	10s	30	0
heat	260°C ± 5°C			
				-
	IPC/ECA J-STD-002			
	Method A dip and look	3 sec dip	66	0
	No aging, solder Ta = 245°C	•		
				
	IPC/ECA J-STD-002			1
	Method B dip and look			
CD	No aging	Q bours		
SD Soldorability	Solder Ta = 245°C	8 hours	66	0
Solderability	>95% lead coverage required	3 sec dip		1
	Steam Aging: condition C			1
	Steam Ta = 93°C, 8 hours Solder Ta = 245°C, 3 sec dip			1
				1
	Dry Bake: Ta = 150°C	16 hours		
	Ta = 150°C	16 hours	66	0
	>95% lead coverage required	3 sec dip		1
*Fither HAST or HT3DB are too				

^{*}Either HAST or HT3RB are tested for a set of devices.

Calculation of FIT and MTBF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB) and High temperature Gate Bias (HTGB). Confidence level 60%, derated to 55°C, activation energy 0.7Ev test time 168 to 1000 hours.

Technology	Quantity	Failure rate	MTBF
T1	462	2.6	3.83E+8